

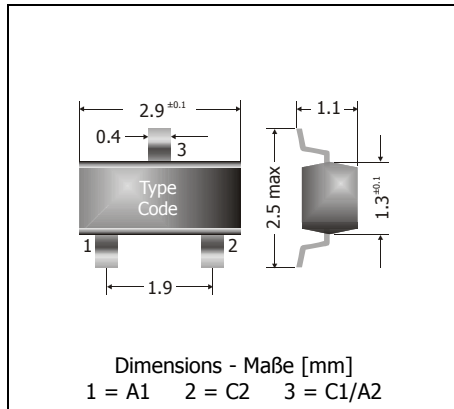


EN: This Datasheet/Document is presented by the manufacturer.

Please visit our website for pricing and availability at www.hestore.hu.

BAV99
Surface Mount Small Signal Double-Diodes
Kleinsignal-Doppel-Dioden für die Oberflächenmontage

Version 2006-07-11



Power dissipation – Verlustleistung

310 mW

Repetitive peak reverse voltage

70 V

Periodische Spitzensperrspannung

Plastic case

SOT-23

Kunststoffgehäuse

(TO-236)

Weight approx. – Gewicht ca.

0.01 g

Plastic material has UL classification 94V-0

Gehäusematerial UL94V-0 klassifiziert

Standard packaging taped and reeled

Standard Lieferform gegurtet auf Rolle

**Maximum ratings (T_A = 25°C)****Grenzwerte (T_A = 25°C)**

per diode / pro Diode		BAV99	
Power dissipation – Verlustleistung ¹⁾		P _{tot}	310 mW ²⁾
Max. average forward current – Dauergrenzstrom (dc)		I _{FAV}	200 mA ²⁾
Repetitive peak forward current – Periodischer Spitzenstrom		I _{FRM}	300 mA ²⁾
Non repetitive peak forward surge current Stoßstrom-Grenzwert	t _p ≤ 1 s	I _{FSM}	0.5 A
	t _p ≤ 1 ms	I _{FSM}	1 A
	t _p ≤ 1 µs	I _{FSM}	2 A
Repetitive peak reverse voltage – Periodische Spitzensperrspannung		V _{RRM}	85 V
Reverse voltage – Sperrspannung (dc)		V _R	70 V
Junction temperature – Sperrschichttemperatur		T _j	-55...+150°C
Storage temperature – Lagerungstemperatur		T _S	-55...+150°C

Characteristics (T_j = 25°C)**Kennwerte (T_j = 25°C)**

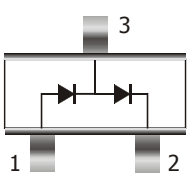
Forward voltage Durchlass-Spannung	I _F = 1 mA		V _F	< 715 mV
	I _F = 10 mA		V _F	< 855 mV
	I _F = 50 mA		V _F	< 1.0 V
	I _F = 150 mA		V _F	< 1.25 V
Leakage current ³⁾ Sperrstrom	T _j = 25°C	V _R = 25 V	I _R	< 30 nA
	T _j = 25°C	V _R = 70 V	I _R	< 2.5 µA
	T _j = 150°C	V _R = 25 V	I _R	< 30 µA
	T _j = 150°C	V _R = 70 V	I _R	< 50 µA

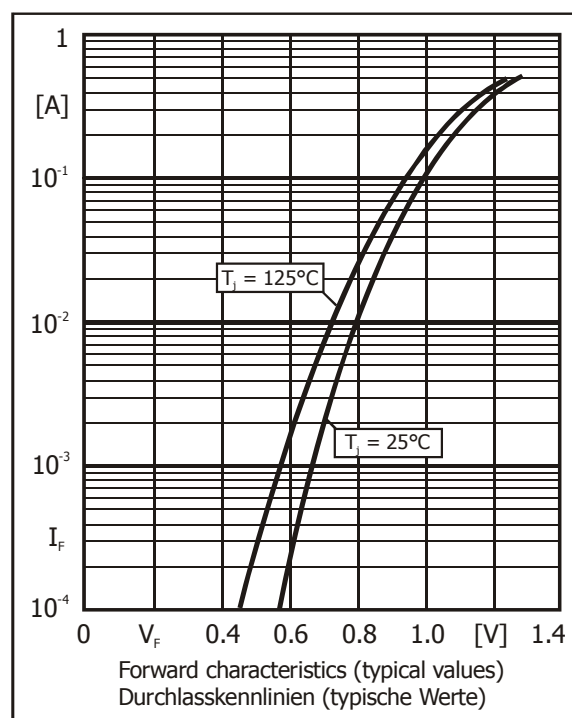
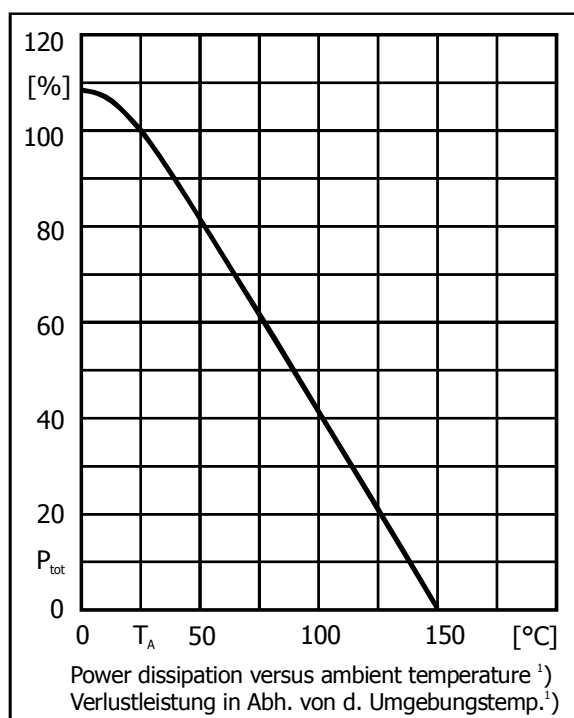
1 Total power dissipation of both diodes – Summe der Verlustleistungen beider Dioden

2 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Lötpad) an jedem Anschluss3 Tested with pulses t_p = 300 µs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 µs, Schaltverhältnis ≤ 2%

Characteristics ($T_J = 25^\circ\text{C}$)
Kennwerte ($T_J = 25^\circ\text{C}$)

Max. junction capacitance – Max. Sperrschichtkapazität $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_T	1.5 pF
Reverse recovery time – Sperrverzögerung $I_F = 10\text{ mA}$ über/through $I_R = 10\text{ mA}$ bis/to $I_R = 1\text{ mA}$	t_{rr}	< 4 ns
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft	R_{thA}	< 400 K/W ¹⁾

Pinning – Anschlussbelegung		Marking – Stempelung
		BAV99 = A7
Double diode, series connection Doppeldiode, Reihenschaltung 1 = A1 2 = C2 3 = C1/A2		
Other available configurations – Andere lieferbare Konfigurationen		
Single diode – einzelne Diode		BAL99
Double diode, common cathode – Doppeldiode, gemeinsame Kathode		BAV70
Double diode, common anode – Doppeldiode, gemeinsame Anode		BAW56



1 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss